



2823/18

Patent
Attorney's Docket No. 015290-502

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Helen H. ZHU et al.) Group Art Unit: 2823
Application No.: 09/820,694) Examiner: J. J. Maldonado
Filed: March 30, 2001) Confirmation No.: 7374
For: METHOD OF PLASMA ETCHING)
SILICON NITRIDE)

AMENDMENT/REPLY TRANSMITTAL LETTER

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Enclosed is a reply for the above-identified patent application.

- ☐ A Petition for Extension of Time is also enclosed.
- ☐ A Terminal Disclaimer and a check for ☐ \$55.00 (248) ☐ \$110.00 (148) to cover the requisite Government fee are also enclosed.
- ☐ Also enclosed is _____.
- ☐ Small entity status is hereby claimed.
- ☐ Applicant(s) request continued examination under 37 C.F.R. § 1.114 and enclose the ☐ \$370.00 (279) ☐ \$740.00 (179) fee due under 37 C.F.R. § 1.17(e).
- ☐ Applicant(s) previously submitted ___, on ___, for which continued examination is requested.
- ☐ Applicant(s) request suspension of action by the Office until at least ___, which does not exceed three months from the filing of this RCE, in accordance with 37 C.F.R. § 1.103(c). The required fee under 37 C.F.R. § 1.17(i) is enclosed.
- ☐ A Request for Entry and Consideration of Submission under 37 C.F.R. § 1.129(a) (146/246) is also enclosed.
- ☐ No additional claim fee is required.

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☒ An additional claim fee is required, and is calculated as shown below:

AMENDED CLAIMS					
	NO. OF CLAIMS	HIGHEST NO. OF CLAIMS PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	ADDT'L FEE
Total Claims	23	MINUS 20 =	3	× \$18.00 (103) =	54.00
Independent Claims	1	MINUS 3 =	0	× \$84.00 (102) =	
If Amendment adds multiple dependent claims, add \$280.00 (104)					
Total Amendment Fee					54.00
If small entity status is claimed, subtract 50% of Total Amendment Fee					
TOTAL ADDITIONAL FEE DUE FOR THIS AMENDMENT					54.00

☐ A claim fee in the amount of \$_____ is enclosed.

☒ Charge \$ 54.00 to Deposit Account No. 02-4800.

The Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17, 1.20(d) and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 02-4800. This paper is submitted in duplicate.

Respectfully submitted,

BURNS, DOANE, SWECKER & MATHIS, L.L.P.

By: _____

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Date: September 19, 2002



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AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Official Action dated July 29, 2002, please amend the present application as follows.

IN THE CLAIMS:

A marked-up version of the claims showing insertions and deletions appears in Appendix A. Please rewrite Claim 1 and add new Claims 21- 23 as follows:

1. (Amended) A process for etching a silicon nitride layer with selectivity to an underlying and/or overlying dielectric layer, comprising the steps of:
introducing a semiconductor substrate into a medium density plasma etching reactor,
the semiconductor substrate having a layer of silicon nitride and an underlying and/or overlying dielectric layer;

B'
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C'